NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE40H21 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

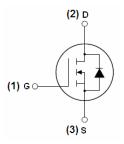
- V_{DS} =40V , I_{D} =210A $R_{DS(ON)}$ <2.2m Ω @ V_{GS} =10V
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



Schematic diagram



Marking and pin assignment



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE40H21	NCE40H21	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	210	А
Drain Current-Continuous(T _C =100°C)	I _D (100℃)	148	Α
Pulsed Drain Current	I _{DM}	840	Α
Maximum Power Dissipation	P_{D}	310	W
Derating factor		2.07	W/℃



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NCE40H21

Single pulse avalanche energy (Note 5)	E _{AS}	1800	mJ
Operating Junction and Storage Temperature Range	T_J, T_STG	-55 To 175	$^{\circ}$

Thermal Characteristic

Thermal Resistance, Junction-to-Case (Note 2)	$R_{ heta JC}$	0.48	°C/W
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Electrical Characteristics (T_A=25°C unless otherwise noted)

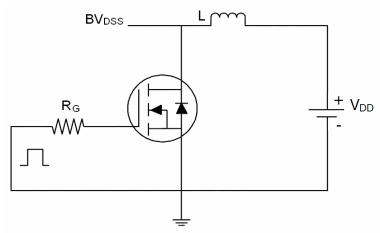
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•			
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	40		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	2	2.7	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =40A	-	1.6	2.2	mΩ
Forward Transconductance	g FS	V _{DS} =24V,I _D =40A	160	-	-	S
Dynamic Characteristics (Note4)			•			
Input Capacitance	C _{lss}	\/ O5\/\/ O\/	-	9500	-	PF
Output Capacitance	Coss	V _{DS} =25V,V _{GS} =0V,	-	1300	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	1000	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	40	-	nS
Turn-on Rise Time	t _r	VDD=30V,ID=2A,RL=15Ω,	-	38	-	nS
Turn-Off Delay Time	t _{d(off)}	RG=2.5Ω,VGS=10V	-	140	-	nS
Turn-Off Fall Time	t _f		-	60	-	nS
Total Gate Charge	Qg		-	250	-	nC
Gate-Source Charge	Q_{gs}	ID=30A,VDD=30V,VGS=10V	-	48	-	nC
Gate-Drain Charge	Q_gd		-	98	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V _{GS} =0V,I _S =40A	-	0.85	1.2	V
Diode Forward Current (Note 2)	Is		-	-	210	Α
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 40A	-	48		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	78		nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

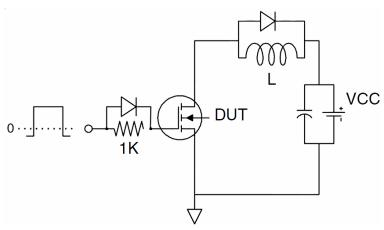
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- **4.** Guaranteed by design, not subject to production
- 5. EAS condition: Tj=25 $^{\circ}\text{C}\,\text{,V}_{DD}\text{=}20\text{V}\text{,V}_{G}\text{=}10\text{V}\text{,L}\text{=}1\text{mH,Rg}\text{=}25\Omega$

Test circuit

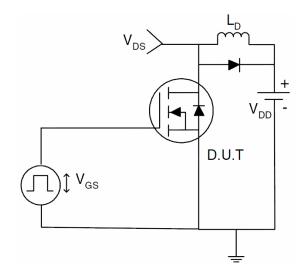
1) E_{AS} test Circuits



2) Gate charge test Circuit:



3) Switch Time Test Circuit:





Typical Electrical and Thermal Characteristics (Curves)

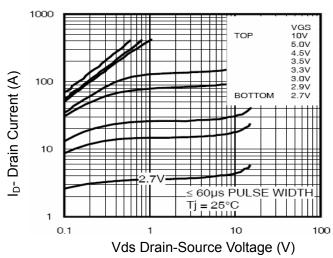


Figure 1 Output Characteristics

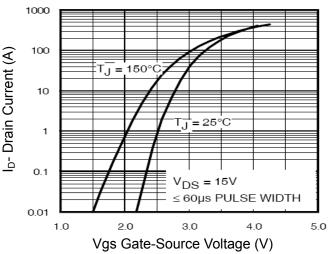


Figure 2 Transfer Characteristics

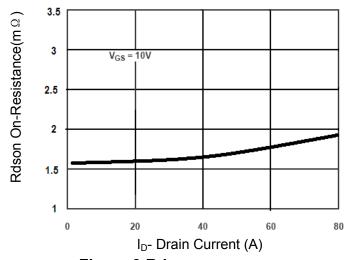


Figure 3 Rdson- Drain Current

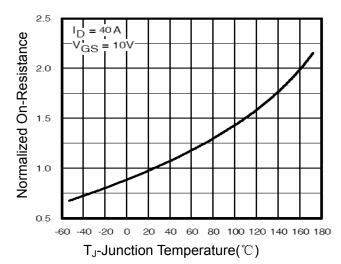


Figure 4 Rdson-JunctionTemperature

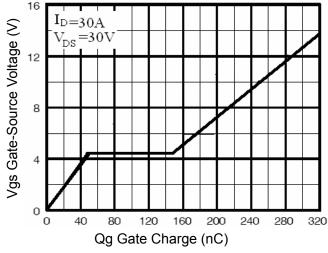


Figure 5 Gate Charge

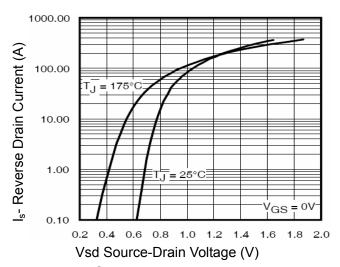


Figure 6 Source- Drain Diode Forward



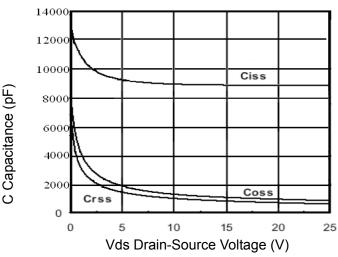
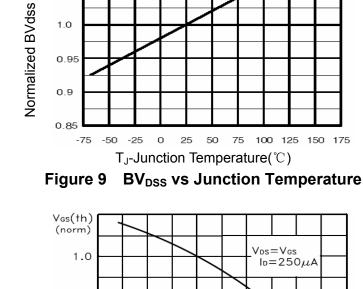
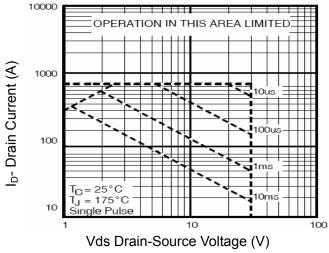


Figure 7 Capacitance vs Vds

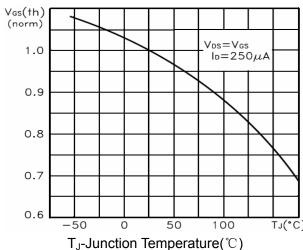


1.1

1.05



Safe Operation Area



50

Figure 10 V_{GS(th)} vs Junction Temperature

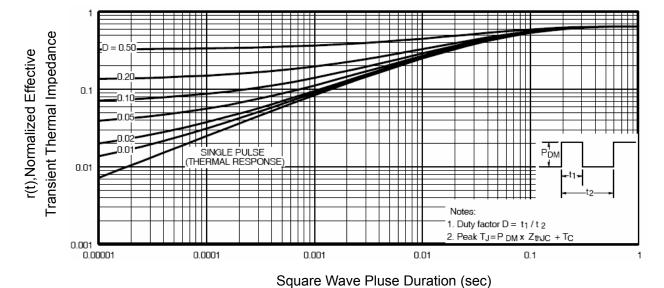
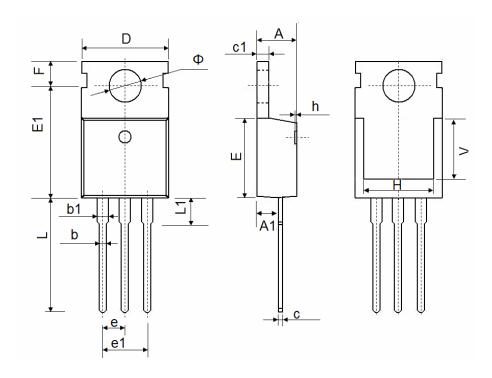


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L Package Information



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
Е	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500	REF.	0.295	REF.	
Ф	3.400	3.800	0.134	0.150	

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